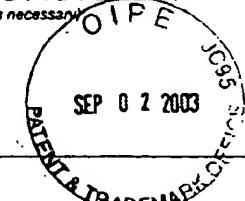


Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Under the Paperwork Reduction Act of 1995, no person is required to respond to a collection of information unless it contains a valid OMB control number.

Complete if Known

Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

Sheet 1 of 1

Attorney Docket No: 1303.029US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
LP	US-6,210,999	04/03/2001	Gardner, , et al.	438	183	12/04/1998
LP	US-6,541,280	04/01/2003	Kaushik, , et al.			03/20/2001

OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite's No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
LP		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000),pp. 531-537	
LP		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000),pp. 105-113	
LP		FERGUSON, J D., et al., "Atomic layer deposition of Al2O3 and SiO2 on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000),pp. 280-292	
LP		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta2O5 films", <u>Journal of the Korean Physical Society</u> , (December 2000),pp. 975-979	
LP		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000),4 pages	
LP		KUKLI, KAUPO , "Atomic Layer Deposition of Titanium Oxide from TiI4 and H2O2", <u>Chemical Vapor Deposition</u> , (2000),pp. 303-310	
LP		KUKLI, KAUPO , et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001),pp. 262-272	
LP		KUKLI, KAUPO , et al., "Real-time monitoring in atomic layer deposition of TiO2 from TiI4and H2O-H2O2", <u>American Chemical Society</u> , (2000),pp. 8122-8128	
LP		LEE, J. , "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al2O3 Gate Dielectric", <u>IEDM</u> , (2000),pp. 645-648	
LP		PARANJPE, AJIT , et al., "Atomic layer deposition of AlOx for thin film head gap application", <u>Journal of the Electrochemical Society</u> , (September 2001),pp. 465-471	
LP		SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis if hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000),2 pages	

EXAMINER

DATE CONSIDERED

12/11/03

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English Language Translation is attached